area to be a light emitting area. Then, a layer containing organic compounds is formed in the area surrounded by the separator by evaporation or ink jet printing. When a full color display is formed, materials are properly selected to form the layer containing the organic compounds. After that, over the separator and the layer containing the organic compounds, a plurality of second wiring lines in stripes is formed with a metal material such as Al or Al alloy (a material to be a cathode) so as to cross the plurality of first wiring lines formed of ITO. According to the steps described above, the peeled layer containing the light emitting diode forming the layer containing the organic compounds into the light emitting layer can be fabricated.

[0141] Subsequently, an encapsulation substrate to be the support is bonded with a sealing material. Alternatively, a protection film is disposed over the second wiring lines for encapsulation.

[0142] Then, the substrate is peeled and the peeled layer containing the light emitting diode is bonded to the transfer object (for example, a glass substrate with a curved surface). The method for peeling the substrate is not defined particularly. It is fine to use the methods shown in the embodiment mode and the embodiment 1 are used.

[0143] In addition, the invention can be implemented not only to the full color display device but also to a monochromatic light emitting device, such as a surface light source and an illumination system.

[0144] Furthermore, the embodiment can be freely combined with the embodiments 1, 3, 4, and 5.

[0145] According to the invention, displays can be installed in various portions with a curved surface (including windows, ceilings, doors and dashboards) in the limited space, such as the driver seat of vehicles, typically automobiles and aircrafts.

What is claimed is:

1. A method for fabricating a semiconductor device comprising:

forming a support with curvature;

forming a transfer object with curvature;

forming a peeled layer containing at least a device over a substrate having higher rigidity than that of the support;

bonding the support with curvature to the peeled layer containing the device with an external force applied so as to match a surface topology of the peeled layer containing the device;

peeling the peeled layer containing the device bonded with the support from the substrate by physical unit; and

bonding the transfer object to the peeled layer containing the device to sandwich the peeled layer containing the device between the support and the transfer object,

wherein the support bonded with the peeled layer containing the device returns into a shape after forming the support with curvature at a time of finishing peeling the peeled layer containing the device bonded with the support from the substrate by physical means.

2. The method for fabricating the semiconductor device according to claim 1, wherein the device includes one kind or a plurality of kinds selected from a thin film transistor and an organic light emitting diode.

3. The method for fabricating the semiconductor device according to claim 1, wherein the support has curvature and elasticity at a time of finishing forming a support with curvature.

4. The method for fabricating the semiconductor device according to a claim 1, wherein $R_i \leqq R_f \leqq R_m$, where a curvature radius of the support after forming a support with curvature is R_i, a curvature radius after bonding the support with curvature to the peeled layer containing the device is R_m, and a curvature radius after peeling the peeled layer containing the device bonded with the support from the substrate is R_f.

5. The method for fabricating the semiconductor device according to a claim 1, wherein the support is an encapsulation material, and the device is an organic light emitting diode.

6. The method for fabricating the semiconductor device according to a claim 1, wherein the support is an opposite substrate and the device has a pixel electrode, in which a liquid crystal material is filled between the pixel electrode and the opposite substrate.

7. The method for fabricating the semiconductor device according to a claim 1, wherein the transfer object has curvature at a time of finishing forming a support with curvature.

8. The method for fabricating the semiconductor device according to a claim 1, wherein at least one of the support and the transfer object is transparent.

9. The method for fabricating the semiconductor device according to a claim 1, wherein curvature radii of the support and the transfer object range from 50 to 200 cm.

10. A method for fabricating a semiconductor device comprising:

forming a support with curvature;

forming a transfer object with curvature;

forming a layer containing at least a device over a substrate having higher rigidity than that of the support;

bonding the support with curvature to the layer containing the device with an external force applied so as to match a surface topology of the layer containing the device;

peeling the layer containing the device bonded with the support from the substrate by physical means; and

bonding the transfer object to the layer containing the device to sandwich the layer containing the device between the support and the transfer object,

wherein the support bonded with the layer containing the device returns into a shape after forming said support with curvature at a time of finishing peeling the layer containing the device bonded with the support from the substrate by physical means.

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